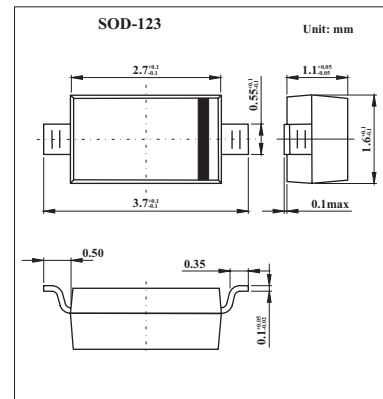


SMALL SIGNAL DIODES

1N4150W

■ Features

- Silicon Epitaxial Planar Diode
- Fast general purpose and switching.
- This diode is also available in other case styles including:
the DO-35 case with the type designation 1N4150 and
the Mini-MELF case with the type designation LL4150.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	50	V
Maximum Average Rectified Current	I_o	200	mA
Maximum Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	410 ⁽¹⁾	mW
Maximum Forward Voltage Drop at $I_F = 200\text{mA}$	V_F	1.0	V
Maximum Reverse Current at $V_R = 50\text{V}$	I_R	100	nA
Maximum Reverse Recovery Time at $I_F = 10$ to 200mA , to 0.1I_F	T_{rr}	4.0	ns
Maximum Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-65 to +150	$^\circ\text{C}$

NOTES::

(1) Valid provided that electrodes are kept at ambient temperature